

DSC5C01

Silicon NPN epitaxial planar type

For low frequency amplification

DSC2C01 in SMini3 type package

■ Features

- High forward current transfer ratio h_{FE} with excellent linearity
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: C9

■ Packaging

DSC5C01×0L Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	100	V
Collector-emitter voltage (Base open)	V_{CEO}	100	V
Emitter-base voltage (Collector open)	V_{EBO}	15	V
Collector current	I_C	20	mA
Peak collector current	I_{CP}	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Operating ambient temperature	T_{opr}	-40 to +85	$^\circ\text{C}$
Storage temperature	T_{slg}	-55 to +150	$^\circ\text{C}$

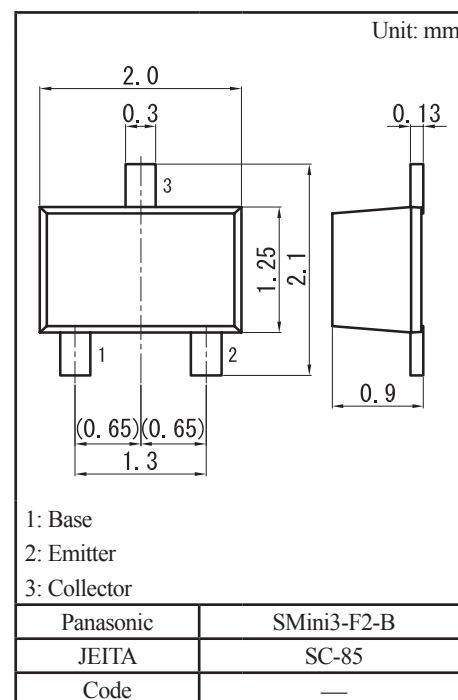
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

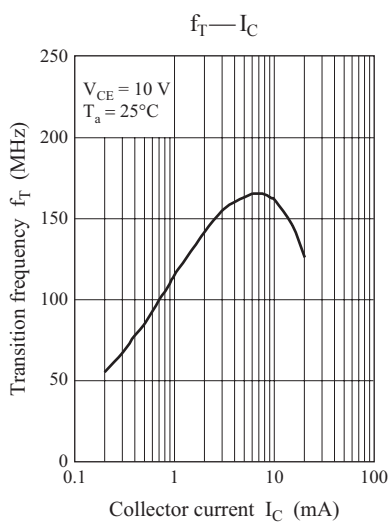
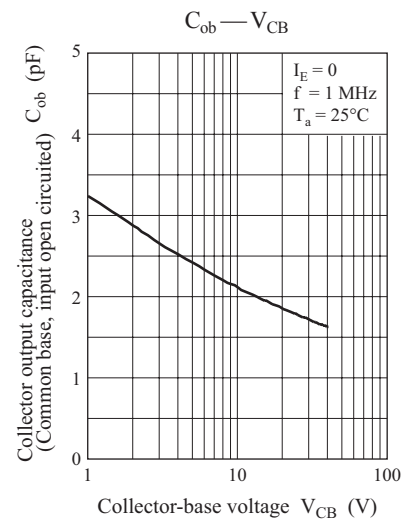
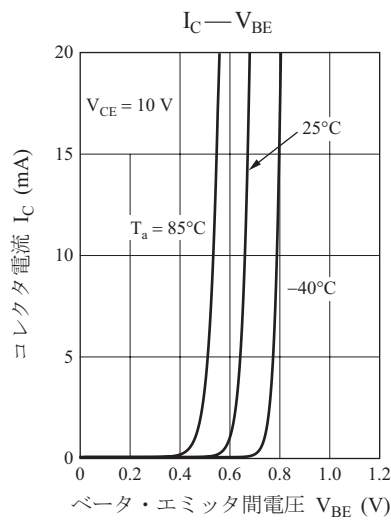
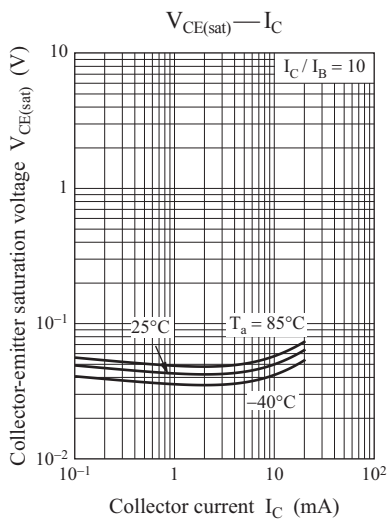
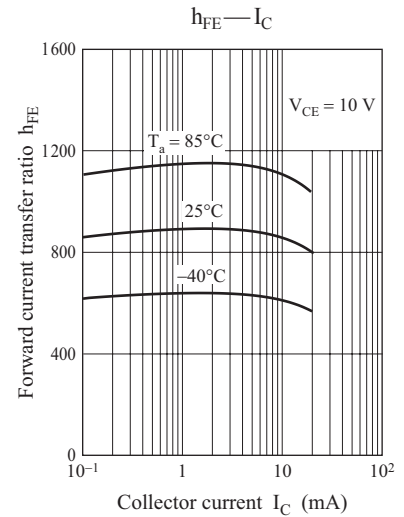
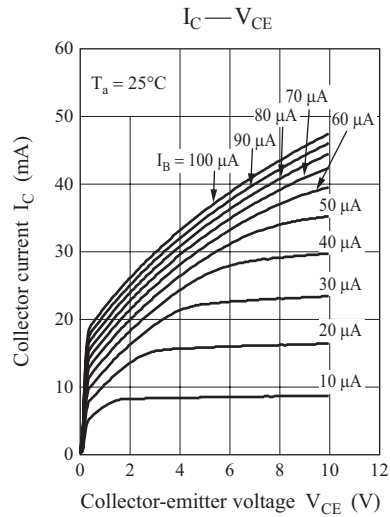
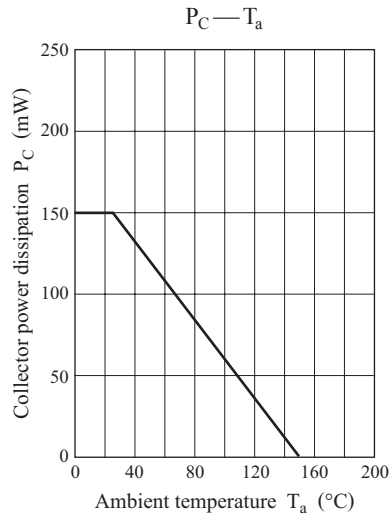
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10\ \mu\text{A}$, $I_E = 0$	100			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 1\ \text{mA}$, $I_B = 0$	100			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10\ \mu\text{A}$, $I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 60\ \text{V}$, $I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 60\ \text{V}$, $I_B = 0$			1	μA
Forward current transfer ratio *1	h_{FE}	$V_{CE} = 10\ \text{V}$, $I_C = 2\ \text{mA}$	400		1 200	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\ \text{mA}$, $I_B = 1\ \text{mA}$		0.05	0.20	V
Transition frequency	f_T	$V_{CE} = 10\ \text{V}$, $I_C = 2\ \text{mA}$		140		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Rank classification

Code	R	S
Rank	R	S
h_{FE}	400 to 800	600 to 1 200
Marking Symbol	C9R	C9S





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